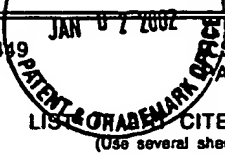
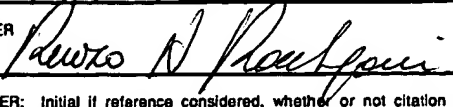
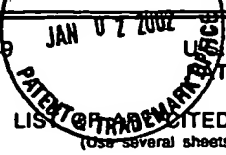
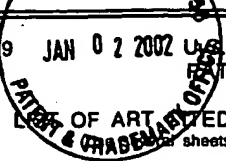




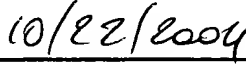


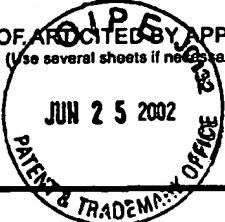
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				FILING DATE August 29, 2001		GROUP 4818, 2525	
U.S. PATENT DOCUMENTS							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
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EXAMINER		DATE CONSIDERED					
[Signature]		10/12/2004					
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				FILING DATE August 29, 2001		GROUP 2816-72825	
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PNC	AA	09/797,635	Moore	—	—	03/01/2001	
	AB	09/732,966	Githen	—	—	12/08/2000	
	AC	09/943,199	Campbell, et al.	—	—	08/29/2001	
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PNC	AK	6,084,796	Kozicki et al.	—	—		
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Form PTO-1449 LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Kristy A. Campbell		RECEIVED		
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LIST OF REFERENCES BY APPLICANT (Use several sheets if necessary)				APPLICANT: Kristy A. Campbell et al.				
				FILING DATE August 29, 2001		GROUP 2848 2829		
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EXAMINER <i>Rebecca N. Rouben</i>				DATE CONSIDERED <i>10/22/2004</i>				
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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	09/943,190	
			Filing Date	August 29, 2001	
			First Named Inventor	Kristy A. Campbell	
			Art Unit	2816 2825	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	8	Attorney Docket Number	M4065.0698/P698

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
PAC	AA	US 2002/0168820	11/14/2002	Kozicki et al.	
PAC	AB	6,469,364	10/22/2002	Kozicki	
PAC	AC	6,388,324	05/14/2002	Kozicki et al.	
PAC	AD	US 2002/0000666	01/03/2002	Kozicki et al.	
PAC	AE	5,500,532	03/19/1996	Kozicki et al.	
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FOREIGN PATENT DOCUMENTS						
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
	BA	WO 97/48032	12/18/1997	Kozicki et al.		
	BB	WO 99/28914	06/10/1999	Kozicki et al.		
	BC					
	BD					

Examiner Signature	<i>Thomas N. Packman</i>	Date Considered	10/22/2004
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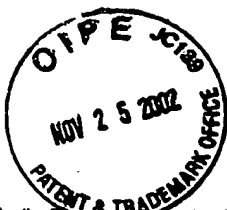
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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	09/943,190
				Filing Date	August 29, 2001
				First Named Inventor	Kristy A. Campbell
				Group Art Unit	2818 2425
				Examiner Name	Not Yet Assigned
Sheet	2	of	8	Attorney Docket Number	M4065.0698/P698

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
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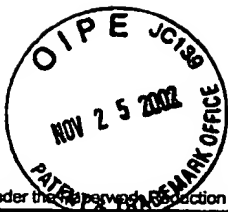
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		Filing Date	August 29, 2001		
		First Named Inventor	Kristy A. Campbell		
		Group Art Unit	2848 7525		
		Examiner Name	Not Yet Assigned		
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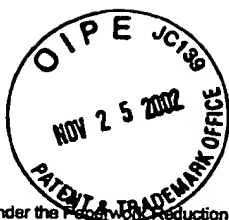


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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	09/943,190
				Filing Date	August 29, 2001
				First Named Inventor	Kristy A. Campbell
				Group Art Unit	2848 2825
				Examiner Name	Not Yet Assigned
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First Named Inventor	Kristy A. Campbell
Group Art Unit	2818 ZJ25
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0698/P698

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Examiner Signature	<i>Rebecca M. Thompson</i>	Date Considered	10/22/2004
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Examiner Name	R. Rocchegiani
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Substitute for form 1449B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	09/943,190
				Filing Date	August 29, 2001
				First Named Inventor	Kristy A. Campbell
				Group Art Unit	2825
				Examiner Name	R. Rocchegiani
				Attorney Docket Number	M4065.0698/P698
Sheet	3	of	3		

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

Examiner Signature	<i>Rocco N. Rocchegiani</i>	Date Considered	10/22/2004
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¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

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U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
MI22-1668SERIAL NO.
09/943.190LIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)

APPLICANT: Kristy A. Compbell et al.

FILING DATE
August 29, 2001GROUP
2818-2825

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Mms	AA	3,622,319	11/23/71	Sharp	96	27	
	AB	3,743,847	07/03/73	Boland	250	510	
	AC	4,269,935	05/26/81	Masters et al.	430	323	
	AD	4,312,938	01/26/82	Drexler et al.	430	496	
	AE	4,320,191	03/16/82	Yoshikawa et al.	430	296	
	AF	4,795,657	01/03/89	Formigoni et al.	427	96	
	AG	4,847,674	07/11/89	Silwa et al.	357	67	
	AH	5,177,567	01/05/93	Klersy et al.	257	4	
	AI	5,219,788	06/15/93	Abernathy et al.	437	187	
	AJ	5,726,083	03/10/98	Takaishi	438	210	
Mms	AK	5,751,012	05/12/98	Wolstenholme et al.	257	5	

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							Yes	No
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Mms	AN		Das et al., <i>Theory of the characteristic curves of the silver chalcogenide glass inorganic photoresists</i> , 54 APPL. PHYS. LETT., No. 18, pp. 1745-1747 (May 1989).
Mms	AO		Helbert et al., <i>Intralevel hybrid resist process with submicron capability</i> , SPIE Vol. 333 SUBMICRON LITHOGRAPHY pp. 24-29 (1982)
Mms	AP		Hilt, DISSERTATION: <i>Materials Characterization of Silver Chalcogenide Programmable Metallization Cells</i> , Arizona State University, pp. title page-114 (UMI Company, May 1999).

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FILING DATE
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ms	AA	5,789,277	08/04/98	Zahorik et al.	438	95	
	AB	5,841,150	11/24/98	Gonzalez et al.	257	3	
	AC	5,920,788	07/06/99	Reinberg	438	466	
	AD	5,998,066	12/07/99	Block et al.	430	5	
	AE	6,077,729	06/20/00	Harshfield	438	128	
	AF	6,236,059 B1	05/22/01	Wolstenholme et al.	257	3	
	AG	6,297,170 B1	10/02/01	Gabriel et al.	438	738	
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	AI	6,316,784 B1	11/13/01	Zahorik et al.	257	3	
	AJ	6,329,606 B1	12/11/01	Freyman et al.	174	260	
ms	AK	6,348,365	02/19/02	Moore et al.	438	130	

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ms	AN	McHardy et al., <i>The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation</i> , 20 J. Phys. C: Solid State Phys., pp. 4055-4075 (1987).
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my	AA	10/077,867		Campbell et al. (as filed)			02/20/2002
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	AC						
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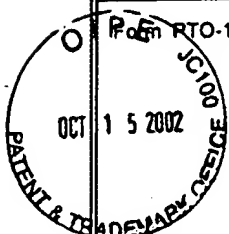
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	LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)			APPLICANT: Kristy A. Campbell et al.			
				FILING DATE August 29, 2001	GROUP 2825		
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EXAMINER <i>Mark S. Lee</i>				DATE CONSIDERED 10/31/07			
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10/31/04

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